Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A semiconductor device comprising:

a substrate having conductive interconnections;

two or more vertically stacked chips on said substrate, each supporting chip having a protective overcoat layer over a first surface and bond pads covered with bond pad caps;

metal standoffs <u>having the same thickness as the bond pad caps disposed on</u>
<u>the first surface, contacting the protective overcoat layer</u> [[thereon]] to separate
[[it]] <u>the supporting chip</u> from the next successive chip; and

a plurality of bond wires connecting at least one chip to said substrate.

- 2. (original) A semiconductor device as in claim 1, wherein said metal standoffs comprise aluminum islands.
- 3. (original) A semiconductor device as in claim 1, wherein the thickness of said metal standoffs is 5 to 20 kA.
- 4. (original) The semiconductor device of claim 1 wherein said standoffs are patterned over the chip passivation layer.
- 5. (original) The semiconductor device of claim 1 wherein said metal standoffs are thermally conductive.
- 6. (original) The semiconductor device of claim 1 wherein said metal standoffs are positioned within the area surrounded by bond pads.
- 7. (original) The semiconductor device of claim 1 wherein a polymeric adhesive secures the first chip to said substrate.
- 8. (original) The semiconductor device of claim 1 wherein bond wires connect more than one chip to said substrate.

- 9. (original) The semiconductor device of claim 1 wherein said substrate is a BGA package substrate.
- 10. (canceled)
- 11. (original) The device of claim 1 wherein said supporting chips include copper bond pads having aluminum caps.

12-18. (canceled)

- 19. (new) The device of claim 1, further comprising a adhesive layer for securing the metal standoffs to the next successive chip.
- 20. (new) The device of claim1 in which the metal standoffs and the bond pad caps have the same etched profile.